

Title (en)
PHOTODETECTOR HAVING A VERY THIN SEMICONDUCTING REGION

Title (de)
PHOTODETEKTOR MIT SEHR DÜNNER HALBLEITENDER REGION

Title (fr)
PHOTODETECTEUR COMPRENANT UNE REGION SEMICONDUCTRICE TRES MINCE

Publication
EP 2368273 B1 20160713 (FR)

Application
EP 09803862 A 20091214

Priority
• FR 2009052526 W 20091214
• FR 0859077 A 20081224

Abstract (en)
[origin: WO2010072942A1] The invention relates to a photodetector that includes at least one portion of a semiconducting layer (33) formed directly on at least a portion of a reflective layer (31) and to be illuminated with a light beam (35), at least one pad (37) being formed on the portion of the semiconducting layer opposite the reflective layer portion, wherein the pad and the reflective layer portion are made of a metal or of a negative permittivity material, the optical cavity formed between said at least one reflective layer portion and said at least one pad has a thickness strictly lower than a quarter of the ratio of the light beam wavelength to the optical index of the semiconducting layer, and typically representing about one tenth of said ratio.

IPC 8 full level
H01L 31/0224 (2006.01)

CPC (source: EP US)
H01L 31/022408 (2013.01 - EP US)

Citation (examination)
US 2008090318 A1 20080417 - FATTAL DAVID [US], et al

Cited by
DE202014010751U1

Designated contracting state (EPC)
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